

PATENT ABSTRACTS OF JAPAN

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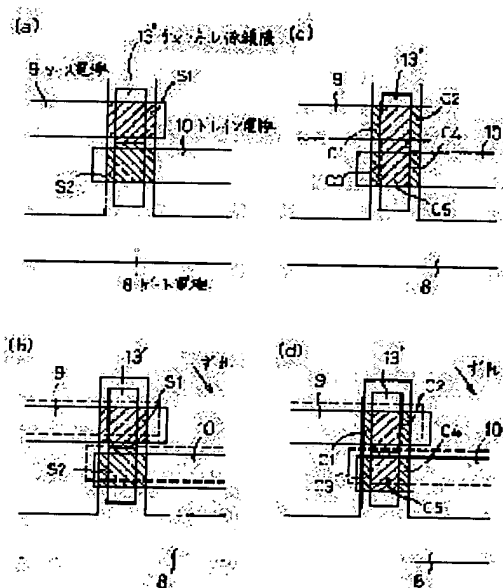
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(54) THIN FILM TRANSISTOR

(57)Abstract:

PURPOSE: To provide a thin film transistor which can improve display quality of a liquid crystal panel, by eliminating irregularity of parasitic capacitance of a thin film transistor.

CONSTITUTION: The channel protecting film 13' of a thin film transistor is formed only on a gate electrode 8. A source electrode 9 and a drain electrode 10 intersect only the two facing sides of a region formed by the channel protecting film 13', and do not overlap with the other sides. The source electrodes 9 and the drain electrode 10 crosswise intersect the gate electrode 8. By this constitution, the value of a parasitic capacitance generated in the part where the thin film transistor is formed can be made constant.



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